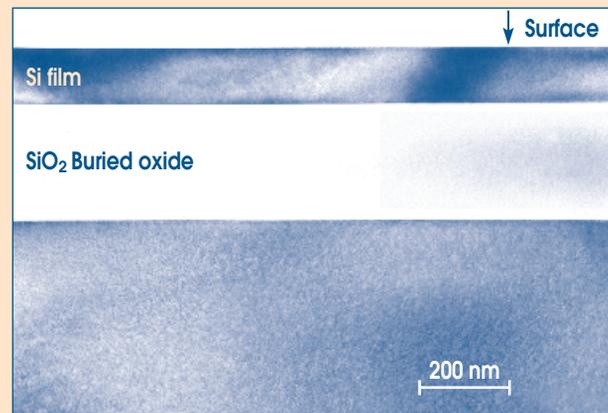
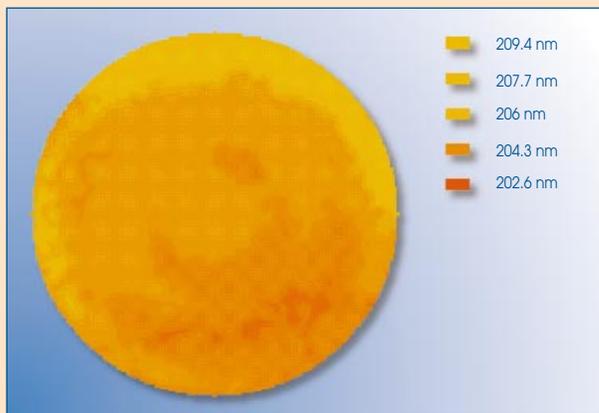




General Specifications for: Standard UNIBOND® Wafers

Parameters	Size		
	4"	6"	8"
SOI thickness	205 nm	205 nm	205 nm
Uniformity (max-min)	< 5%	< 5%	< 5%
Top Layer	Type	CZ, P type	CZ, P type
	Resistivity	14-22 ohms.cm	14-22 ohms.cm
	Orientation	<100>	<100>
Box thickness	400 nm	400 nm	400 nm
Uniformity (max-min)	< 2.5%	< 2.5%	< 2.5%
Base Wafer	Type	CZ, P type	CZ, P type
	Resistivity	14-22 ohms.cm	14-22 ohms.cm
	Orientation	<100>	<100>
	Thickness	525 μm	625 μm
Dislocation Density	< 100/cm ²	< 100/cm ²	< 100/cm ²
Pipe Density	none	none	none
Roughness (rms)		< 2 Å	< 2 Å
	(max-min)	< 15 Å	< 15 Å
Metal Contamination	< 5.10 ¹⁰ /cm ²	< 5.10 ¹⁰ /cm ²	< 5.10 ¹⁰ /cm ²
Bonding Exclusion	< 3 mm	< 3 mm	< 3 mm



Typical applications: partially or fully depleted CMOS applications

- high-speed / low-power / low-voltage ICs
- « Systems on chip »
- High-temperature electronics
- Radiation-hardened circuits